

SPT02-236DDB

Automation sensor transient and overvoltage protection

Datasheet - production data



Features

- Double diode array for switch protection and reverse blocking protection
- 6 V to 36 V supply voltage range
- Minimum breakdown voltage V_{BR}: 38 V
- 8/20 μs 2 A maximum clamping voltage: 46 V
- Blocking diode drop forward voltage V_F: 1.1 V at 300 mA
- Blocking diode maximum 10 ms square pulse current I_{ESM}: 3 A
- Ambient temperature: -40 °C to +100 °C
- µQFN 2L 0.8 mm flat package

Complies with following standards

- Voltage surge: IEC 61000-4-5, R_{CC} = 500 Ω, ±1 kV
- Electrostatic discharge, IEC 61000-4-2:
 - ±8 kV contact discharge
 - ±15 kV air discharge
- Electrical transient immunity: IEC 61000-4-4: ±2 kV

Benefits

- Compliant for interface with logic input type 1, 2 and 3 IEC 61131-2 standard
- Highly compact with integrated power solution in SMD version

Applications

- Factory automation sensor application
- · Proximity sensor interface protection
- Transient and surge voltage protection
- Compliant with sensor standard, EN 60947-5-2

Description

The SPT02 is specifically designed for the protection of 24 V proximity sensors. It implements the reverse polarity and the overvoltage protection of the sensor power supply and the power switch overvoltage protection.

It provides a very compact and flexible solution.

Thanks to high performance ST technology, the SPT02 protects the proximity sensor to the highest level compliant with IEC 61000-4-2, IEC 61000-4-4 and IEC 61000-4-5 standards.

Figure 1. Functional diagram (top view)

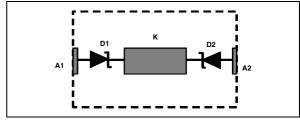
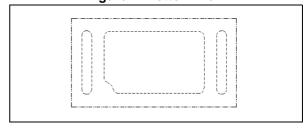


Figure 2. Bottom view



Basic application SPT02-236DDB

1 Basic application

Sensor **Process control** P.supply $\mathbf{v}_{\!cc}$ Detector LS D2 **太** D1 GND HS Load Load **Detector** D2 Vcc **太** D1 HS **GND** P.supply **Process control** Sensor

Figure 3. STP02 configuration

SPT02-236DDB Characteristics

2 Characteristics

Table 1. Pinout connections⁽¹⁾

Symbol	Description	
K	D1 power bus protection diode cathode and D2 reverse blocking protection cathode	
A1	D1 power bus protection diode anode	
A2	D2 reverse blocking protection anode	

^{1.} See Figure 1

Table 2. Absolute ratings ($T_{amb} = 25 \text{ °C}$)

Symbol	Diode	Parameter	Value	Unit
	All	ESD protection, IEC 61000-4-2, per diode, in air ⁽¹⁾	30	kV
V _{PP}	All	ESD protection, IEC 61000-4-2, per diode, in contact (1)	30	kV
V _{PP}	All	Peak Surge Voltage, IEC 61000-4-5, per diode, R_{CC} = 500 Ω , ⁽¹⁾	1	kV
P _{PP}	All	Peak pulse current, $T_J = T_{amb} = 85 ^{\circ}\text{C}$, $t_P = 8/20 \mu\text{s}$	1400	W
I _{PP}	All	Peak pulse power dissipation, $T_J = T_{amb} = 85$ °C, $t_P = 8/20 \ \mu s$	25	Α
I _{FSM}	All	Maximum forward surge current, t _P = 10 ms square	3	Α
E _{AR}	D1	Maximum repetitive avalanche energy L= 1 H, I_{RAS} = 0.3A, R_S = 100 Ω , V_{CC} = 30 V, T_{amb} = 85 °C, ⁽¹⁾	66	mJ
T _J	All	Storage junction temperature range	- 40 to 150	°C

^{1.} See system oriented test circuits in *Figure 5* (ESD) and *Figure 4* (Surge as also described in IEC 60947-5-2).

Table 3. Recommended operating conditions

Symbol	Parameter	Value	Unit
V _{CC}	Operating power bus supply voltage	-30 to 35	V
100	Pulse repetitive voltage t_P = 0.5 s, R_{CC} = 500 Ω	-30 to 37	V
I _F	D2 forward peak current T _j = 150 °C duty cycle = 50%	300	mA
T _{amb}	Operating ambient temperature range	-40 to 100	°C
T _J	Operating junction temperature range ⁽¹⁾	-40 to 150	°C

^{1.} Extended from DC operating at 150 $^{\circ}\text{C}$ up to peak repetitive value during the inductive load demagnetization

Characteristics SPT02-236DDB

Table 4. Thermal resistance

Symbol	Parameter	Value	Unit
Rth(j-a)	SMD thermal resistance junction to ambient, per diode FR4 board, copper thickness = 35 µm, recommended footprint	230	°C/W
Zth(j-a)	SMD thermal transient impedance junction to ambient, per diode $t_p = 15$ ms, $T_{amb} = 85$ °C, recommended footprint	6.5	°C/W

Table 5. Electrical characteristics ($T_J = 25$ °C, unless otherwise specified)

Symbol	Diode	Name	Test conditions		Value	Unit	
.//	ALL	L Reverse stand off voltage	I _R = 200 nA	MIN	33	\/	
V _{RM}	ALL		I _R = 1 μA	MIN	36	V	
		L Leakage reverse current	$V_{RM} = 36 V^{(1)}$	MAX	1	μA	
I _{RM}	ALL		V _{RM} = 36 V, T _J = 150 °C	MAX	5	μΑ	
V	V _{BR} ALL	Reverse breakdown voltage	I _R = 1 mA	MIN	38	V	
V BR				TYP	41.4	V	
V	.,	De ale alamain a calta as	I _{PP} = 2 A, t _P = 8 /20 μs	MAX	46	V	
V _{CL}	ALL	Peak clamping voltage		TYP	44	V	
R _D	ALL	8/20µs dynamic resistance		TYP	0.5	Ω	
αΤ	ALL	V _{BR} Temperature sensitivity ⁽²⁾		MAX	17	10 ⁻⁴ /°C	
V _{CL}	D1	Peak clamping voltage	I _R = 0.3 A, L = 1 H, V _{CC} = 30 V	MAX	46	V	
V _F	D2	Forward drop voltage	I _F = 300 mA	MAX	1.1	V	

^{1.} Voltage applied at the nodes of each diode

^{2.} V_{BR} @ $T_J = V_{BR}$ @25 °C x (1+ αT x (T_J - 25))

3 System related electromagnetic compatibility ratings

Figure 4. Surge Voltage test circuit according to IEC 61000-4-5 with 500 Ω serial resistor

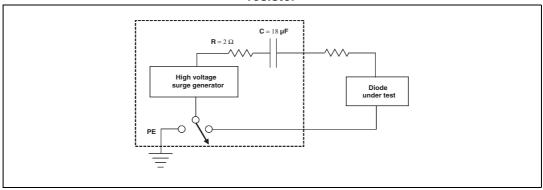


Figure 5. ESD test circuit according to IE 61000-4-2

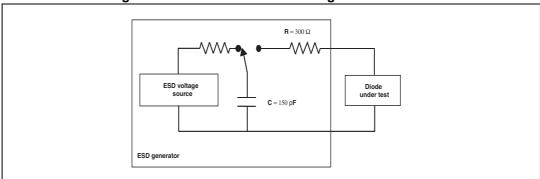
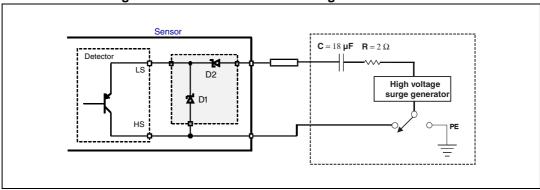


Figure 6. EOS test circuit according to IE 61000-4-5



4 Evaluation of the clamping voltage

$$V_{BR} (T_J) = V_{BR} (25) \times (1 + \alpha T (T_J - 25))$$

 $V_{CL MAX} (8/20 \mu s) = V_{BR MAX} + R_D \times I_{PP}$



5 Application considerations

5.1 Demagnetization of an inductive load driven by the switch protection diode.

The turn off energy EOFF that could be dissipated in the D1 diode is calculated as shown in AN587 and AN1351 application notes:

$$\mathsf{E}_{\mathsf{OFF}} = \mathsf{V}_{\mathsf{BR}} \; \mathsf{x} \; \mathsf{L} \; / \; / \; (\mathsf{R}_{\mathsf{S}})^2 \; \mathsf{x} \; [\mathsf{V}_{\mathsf{CC}} \; + \; (\mathsf{V}_{\mathsf{CC}} \; - \; \mathsf{V}_{\mathsf{BR}}) \; \mathsf{x} \; \mathsf{In} \; (\mathsf{V}_{\mathsf{BR}} \; / \; (\mathsf{V}_{\mathsf{BR}} \; - \; \mathsf{V}_{\mathsf{CC}}))]$$

$$t_{OFF} = L x ln (V_{BR} / (V_{BR} - V_{CC})) / R_{S}$$

 $P_{OFF} = E_{OFF} / t_{OFF}$

With L = 1 H; I = 0.3 A; V_{BR} = 39 V; V_{CC} = 30 V, R_S = 100 Ω the stress withstood by D_1 becomes:

 $E_{OFF} = 65 \text{ mJ}$; $t_{OFF} = 15 \text{ ms}$; $P_{OFF} = 4.3 \text{ W}$

In a single pulse mode operation, the junction temperature can be fairly estimated:

$$T_J = T_{amb} + [Z_{TH}(t_{OFF}) \times P_{OFF}]$$

In a repetitive operation with an F repetitive rate,

$$P_{AV} = E_{OFF} \times F$$

$$T_{J_AV} = T_{amb} + P_{AV} \times R_{TH_JA}$$

And during the demagnetization t_{OFF} , $T_{J-PK} < T_{J-AV} + P_{OFF} \times Z_{TH}$ (t_{OFF})

 Z_{TH} is the transient thermal impedance of each diode for a pulse having a duration t_{OFF} .

Switch V_{BR} D1 V_{CC}

Figure 7. Electrical diagram for inductive load demagnetization

5.2 Life time considerations

Life time of the product is calculated to exceed 10 years. The key parameters to consider are the ambient temperature (T_{amb} < 100 °C), the power supply voltage (V_{CC} < 30 V), and the current in the reverse blocking diode (I_F = 0.1 A switching at 0.5 Hz with 50% duty cycle, the stand-by current being less than 1.5 mA).

For higher current or higher switching frequency operation, the life time should be calculated considering the peak and average junction temperature.

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6 Package information

- Epoxy meets UL94,V0
- Lead-free package

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 8. µQFN-2L dimensions (definitions)

Table 6. µQFN-2L dimensions (values)

	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	0.70	0.75	0.80	0.027	0.029	0.031
A1	0.00	0.02	0.05	0.00	0.001	0.002
b	0.25	0.30	0.35	0.010	0.011	0.014
D	-	3.30	-	-	0.13	-
D2	1.85	2.00	2.10	0.073	0.079	0.082
E	-	1.50	-	-	0.06	-
E2	0.90	1.05	1.16	0.035	0.041	0.046
е	-	2.8	-	-	0.110	-
L	0.97	1.07	1.18	0.038	0.042	0.046

Package information SPT02-236DDB

2.00

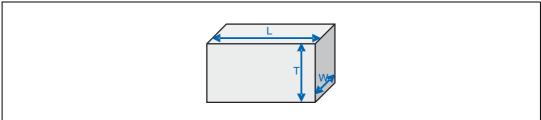
Figure 9. Footprint (dimensions in mm)

7 Recommendation on PCB assembly

7.1 Stencil opening design

- 1. General recommendation on stencil opening design
 - a) Stencil opening dimensions: L (Length), W (Width), T (Thickness).

Figure 10. Stencil opening dimensions



b) General design rule

Stencil thickness (T) = 75 \sim 125 μ m

Aspect Ratio =
$$\frac{W}{T} \ge 1.5$$

Aspect Area =
$$\frac{L \times W}{2T(L + W)} \ge 0.66$$

- 2. Reference design
 - a) Stencil opening thickness: 100 µm
 - b) Stencil opening for central exposed pad: Opening to footprint ratio is 50%.
 - c) Stencil opening for leads: Opening to footprint ratio is 90%.

7.2 Solder paste

- 1. Halide-free flux qualification ROL0 according to ANSI/J-STD-004.
- 2. "No clean" solder paste is recommended.
- 3. Offers a high tack force to resist component movement during high speed.
- 4. Solder paste with fine particles: powder particle size is 20-45 μm.

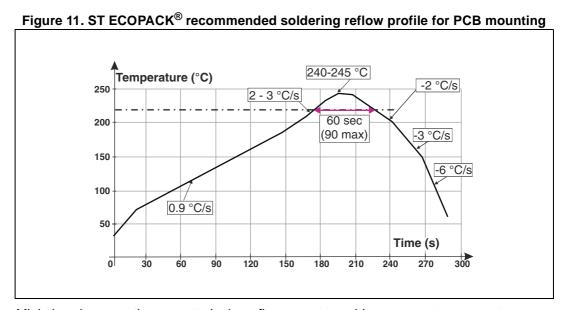
7.3 Placement

- 1. Manual positioning is not recommended.
- 2. It is recommended to use the lead recognition capabilities of the placement system, not the outline centering.
- 3. Standard tolerance of ± 0.05 mm is recommended.
- 4. 3.5 N placement force is recommended. Too much placement force can lead to squeezed out solder paste and cause solder joints to short. Too low placement force can lead to insufficient contact between package and solder paste that could cause open solder joints or badly centered packages.
- 5. To improve the package placement accuracy, a bottom side optical control should be performed with a high resolution tool.
- 6. For assembly, a perfect supporting of the PCB (all the more on flexible PCB) is recommended during solder paste printing, pick and place and reflow soldering by using optimized tools.

7.4 PCB design preference

- 1. To control the solder paste amount, the closed via is recommended instead of open vias.
- The position of tracks and open vias in the solder area should be well balanced. The symmetrical layout is recommended, in case any tilt phenomena caused by asymmetrical solder paste amount due to the solder flow away.

7.5 Reflow profile



Note: Minimize air convection currents in the reflow oven to avoid component movement.

Compliant with J-STD-020D soldering profile

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SPT02-236DDB Ordering information

8 Ordering information

Figure 12. Ordering information scheme

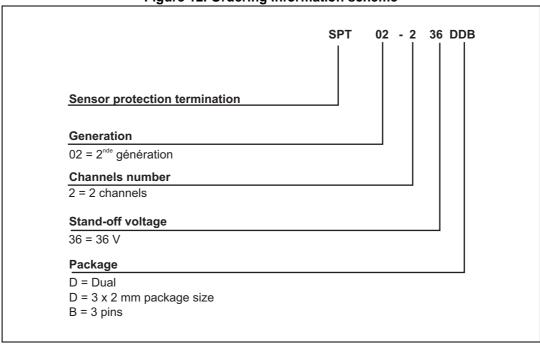


Table 7. Ordering information

Order code Marking		Package	Weight	Packing
SPT02-236DDB	S2	μQFN-2L with exposed pad	15.55 mg	Tape and reel

9 Revision history

Table 8. Document revision history

Date	Revision	Changes	
06-May-2013	1	First issue	
21-Mar-2014	2	Updated Table 2, Table 6 and Figure 9.	

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